

FDR6580

N-Chennal 2.5V Specified PowerTrench™ MOSFET

General Description

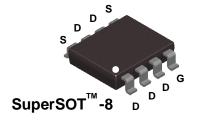
This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

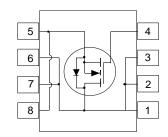
Applications

- · Load switch
- · Motor driving
- Power Management

Features

- 11 A, 20 V. $R_{DS(ON)} = 0.009 \ \Omega \ @V_{GS} = 4.5 \ V$ $R_{DS(ON)} = 0.013 \ \Omega \ @V_{GS} = 2.5 \ V.$
- · Low gate charge.
- High performance trench technology for extremely low $\mathbf{R}_{\text{\tiny DS/ION)}}.$
- Small footprint (38% smaller than a standard SO-8); low profile package (1 mm thick); power handling capability similar to SO-8.





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage	20	V	
V _{GSS}	Gate-Source Voltage		<u>+</u> 8	V
I _D	Drain Current - Continuous	(Note 1a)	11	А
	- Pulsed		50	
P _D	Power Dissipation for Single Operation	(Note 1a)	1.8	W
		(Note 1b)	1.0	
		(Note 1c)	0.9	1
T _J , T _{stg}	Operating and Storage Junction Temperatur	-55 to +150	∘C	

Thermal Characteristics

$R_{\theta^{JA}}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	70	∘C/W
R _{OJC}	Thermal Resistance, Junction-to-Case	(Note 1)	20	∘C/W

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
.6580	FDR6580	13"	12mm	3000 units

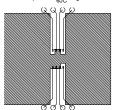
©1999 Fairchild Semiconductor Corporation FDR6580, Rev. A

Electrical Characteristics T_A=25°C unless otherwise noted

OFF CHARACTERISTICS BV _{DSS} Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ μA}$ 20 I_{DSS} Zero Gate Voltage Drain Current $V_{DS} = 16 \text{ V}$, $V_{GS} = 0 \text{ V}$ 1 I_{GSSF} Gate-Body Leakage, Forward $V_{GS} = 8 \text{ V}$, $V_{DS} = 0 \text{ V}$ 10 I_{GSSR} Gate-Body Leakage, Reverse $V_{GS} = -8 \text{ V}$, $V_{DS} = 0 \text{ V}$ -10 ON CHARACTERISTICS (Note 2) $V_{GS(TH)}$ Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \text{ μA}$ 0.4 1.5 $R_{DS(ON)}$ Static Drain-Source On-Resistance $V_{GS} = 4.5 \text{ V}$, $V_{DS} = 11 \text{ A}$ On-Resistance 0.009 On-Resistance 0.013 $I_{D(ON)}$ On-State Drain Current $V_{GS} = 4.5 \text{ V}$, $V_{DS} = 5 \text{ V}$ 25 DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS I_S Maximum Continuous Drain-Source Diode Forward Current 1.5 V_{SD} Drain-Source Diode Forward VGLeach Current 1.5	Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
$ \begin{array}{ c c c c c c c c c } \hline I_{DSS} & Zero \ Gate \ Voltage \ Drain \ Current & V_{DS} = 16 \ V, \ V_{GS} = 0 \ V & 1 \\ \hline I_{GSSF} & Gate-Body \ Leakage, \ Forward & V_{GS} = 8 \ V, \ V_{DS} = 0 \ V & 10 \\ \hline I_{GSSR} & Gate-Body \ Leakage, \ Reverse & V_{GS} = -8 \ V, \ V_{DS} = 0 \ V & -10 \\ \hline \hline ON \ CHARACTERISTICS & (Note 2) & $	OFF CH	ARACTERISTICS					
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V
IGSSR Gate-Body Leakage, Reverse $V_{GS} = -8 \text{ V}$, $V_{DS} = 0 \text{ V}$ -10 ON CHARACTERISTICS (Note 2) $V_{GS(TH)}$ Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \mu A$ 0.4 1.5 $R_{DS(ON)}$ Static Drain-Source On-Resistance $V_{GS} = 4.5 V$, $I_D = 11 A$ On-Resistance 0.009 On-Resistance 0.013 $I_{D(ON)}$ On-State Drain Current $V_{GS} = 4.5 V$, $V_{DS} = 5 V$ 25 DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS I_S Maximum Continuous Drain-Source Diode Forward Current 1.5 V_{SD} Drain-Source Diode Forward $V_{GS} = 0 V$, $I_S = 1.5 A$ (Note 2) 1.2	I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 16 V, V _{GS} = 0 V			1	μΑ
ON CHARACTERISTICS (Note 2) $V_{GS(TH)}$ Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 250 \mu A$ 0.4 1.5 $R_{DS(ON)}$ Static Drain-Source On-Resistance $V_{GS} = 4.5 V$, $I_D = 11 A$ Onder On-Resistance 0.009 On-Resistance 0.009 On-Resistance 0.013 $I_{D(ON)}$ On-State Drain Current $V_{GS} = 4.5 V$, $V_{DS} = 5 V$ 25 DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS I_S Maximum Continuous Drain-Source Diode Forward Current 1.5 V_{SD} Drain-Source Diode Forward $V_{GS} = 0 V$, $I_S = 1.5 A$ (Note 2) 1.2	I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 8 V, V _{DS} = 0 V			10	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = -8 V, V _{DS} = 0 V			-10	μА
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.4		1.5	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.4		1.5	V
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS Is Maximum Continuous Drain-Source Diode Forward Current 1.5 VsD Drain-Source Diode Forward Vss = 0 V, Is = 1.5 A (Note 2) 1.2	R _{DS(ON)}		, 5				Ω
I_S Maximum Continuous Drain-Source Diode Forward Current 1.5 V_{SD} Drain-Source Diode Forward $V_{GS} = 0 \text{ V}$, $I_S = 1.5 \text{ A}$ (Note 2) 1.2	$I_{D(ON)}$	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	25			Α
V_{SD} Drain-Source Diode Forward $V_{GS} = 0 \text{ V}, I_S = 1.5 \text{ A}$ (Note 2) 1.2	DRAIN-S	SOURCE DIODE CHARACTE	RISTICS AND MAXIMUM R	ATING	S		
	Is	Maximum Continuous Drain-Source	e Diode Forward Current			1.5	Α
1 1 1	V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.5 A (Note 2)			1.2	٧

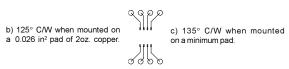
Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,IC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



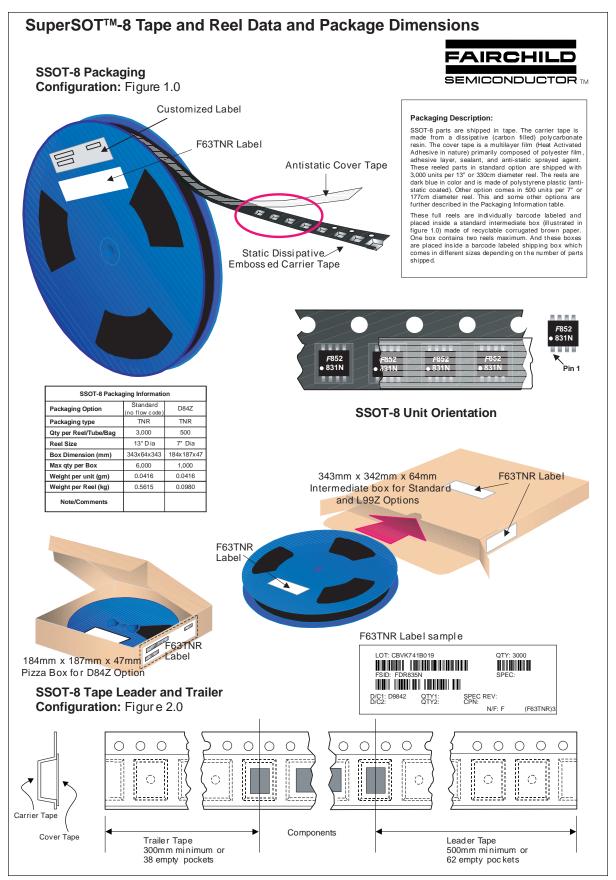
a) 70° C/W when mounted on a 1.0 in² pad of 2 oz. copper.

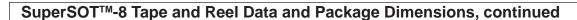




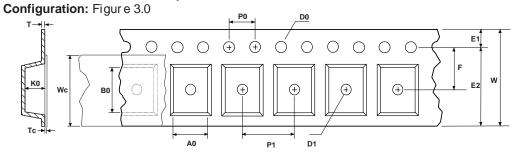
Scale 1 : 1 on letter size paper

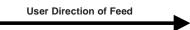
2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%





SSOT-8 Embossed Carrier Tape



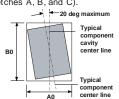


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SSOT-8 (12mm)	4.47 +/-0.10	5.00 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.280 +/-0.150	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

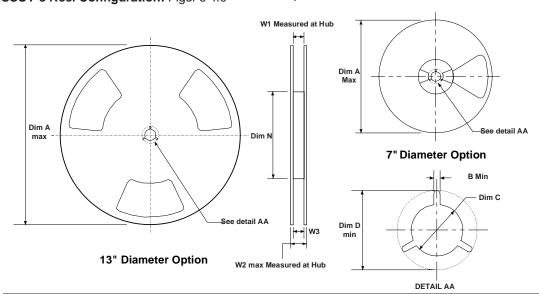


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

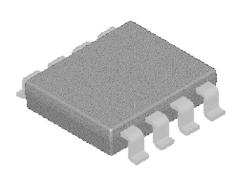
SSOT-8 Reel Configuration: Figur e 4.0

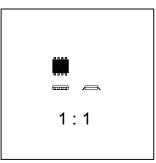


	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	

SuperSOT™-8 Tape and Reel Data and Package Dimensions, continued

SuperSOT™-8 (FS PKG Code 34, 35)

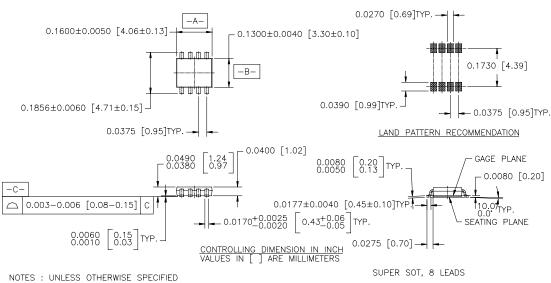




Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0416



STANDARD LEAD FINISH TI BE 200 MICROINCHES / 5.08 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.

2. NO JEDEC REGISTRATION AS JAN. 1996

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